

# **ZXTN19020DG 20V NPN high gain transistor in SOT223**

#### Summary

 $BV_{CEX} > 70V$ 

 $BV_{CEO} > 20V$ 

 $BV_{ECO} > 4.5V$ 

 $I_{C(cont)} = 9A$ 

V<sub>CE(sat)</sub> < 35mV @ 1A

 $R_{CE(sat)} = 20m\Omega$ 

 $P_{D} = 3.0W$ 



#### Complementary part number ZXTP19020DG

## **Description**

Packaged in the SOT223 outline this new low saturation NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

#### **Features**

- Higher power dissipation SOT223 package
- · High gain
- · High peak current
- Low saturation voltage
- · 70V forward blocking voltage
- 4.5V reverse blocking voltage

#### **Applications**

- · DC DC converters
- Motor drive
- · Relay, lamp and solenoid drive
- · Regulator circuits

**Ordering information** 

# Device Reel size (inches) Tape width (mm) Quantity per reel ZXTN19020DGTA 7 12 1000

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Pinout - top view

#### **Device marking**

ZXTN19020D

# **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V <sub>CBO</sub>	70	V
Collector-Emitter voltage (forward blocking)	V <sub>CEX</sub>	70	V
Collector-Emitter voltage	V <sub>CEO</sub>	20	V
Emitter-Collector voltage (reverse blocking)	V <sub>ECX</sub>	6	V
Emitter-Base voltage	V <sub>EBO</sub>	7	V
Continuous Collector current <sup>(c)</sup>	I <sub>C</sub>	9	Α
Base current	I <sub>B</sub>	1	Α
Peak pulse current	I <sub>CM</sub>	20	Α
Power dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1.2	W
Linear derating factor		9.6	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.6	W
Linear derating factor		12.8	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(c)</sup>	P <sub>D</sub>	3.0	W
Linear derating factor		24	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(d)</sup>	P <sub>D</sub>	5.3	W
Linear derating factor		42	mW/°C
Power dissipation at T <sub>C</sub> =25°C <sup>(e)</sup>	P <sub>D</sub>	9.4	W
Linear derating factor		75	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

#### Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	104	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	78	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	42	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	23.5	°C/W
Junction to case <sup>(e)</sup>	$R_{\Theta JC}$	12.3	°C/W

#### NOTES:

<sup>(</sup>a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

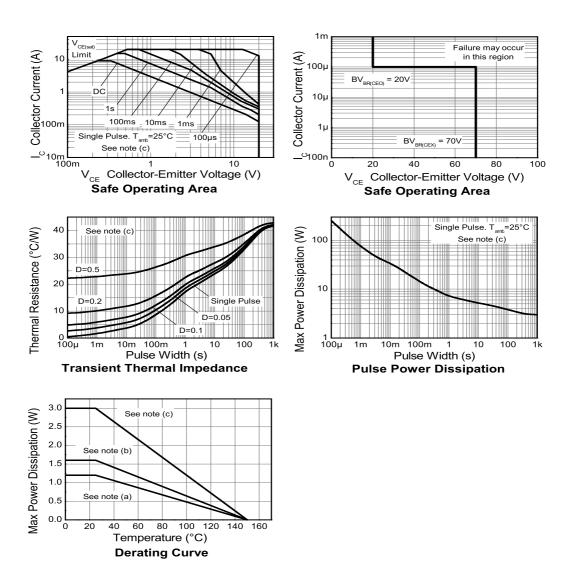
<sup>(</sup>b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

<sup>(</sup>d) As (c) above measured at t<5 seconds.

<sup>(</sup>e) Junction to case (collector tab). Typical

#### Thermal characteristics



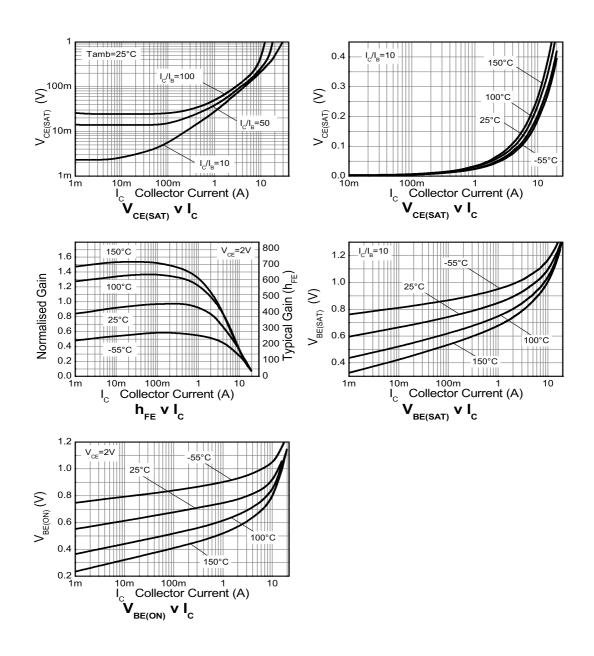
# Electrical characteristics (at $T_{amb} = 25$ °C unless otherwise stated).

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base breakdown	BV <sub>CBO</sub>	70	100		V	$I_C = 100 \mu A$
voltage Collector-Emitter	BV <sub>CEX</sub>	70	100		V	$I_C$ = 100μA, $R_{BF}$ < 1k $\Omega$
breakdown voltage	D CEX	70	100		V	$C = 100\mu A, \text{ MBE} < 1822$
(forward blocking)						-1V < V <sub>BE</sub> < 0.25V
Collector-Emitter	BV <sub>CEO</sub>	20	30		V	I <sub>C</sub> = 10mA <sup>(*)</sup>
breakdown voltage					.,	
Emitter-Collector breakdown voltage	BV <sub>ECX</sub>	6	8.4		V	$I_E = 100 \mu A$ , $R_{BC} < 1 kΩ$
(reverse blocking)						or 0.25V > V <sub>BC</sub> > -0.25V
Emitter-Collector	BV <sub>ECO</sub>	4.5	5.7		V	$I_F = 100 \mu A$
breakdown voltage	- 1200				-	- Ε 100 μα 1
(reverse blocking)						
Emitter-Base breakdown voltage	BV <sub>EBO</sub>	7	8.4		V	$I_E = 100 \mu A$
Collector-Base cut-off	I <sub>CBO</sub>		<1	50	nA	V <sub>CB</sub> = 70V
current				0.5	μΑ	$V_{CB} = 70V, T_{amb} = 100^{\circ}C$
Collector-Emitter cut-off	I <sub>CEX</sub>			100	nA	$V_{CE} = 70V$ , $R_{BE} < 1k\Omega$ or
current					_	-1V < V <sub>BE</sub> < 0.25V
Emitter cut-off current	I <sub>EBO</sub>		<1	50	nA	V <sub>EB</sub> = 5.6V
Collector-Emitter	V <sub>CE(sat)</sub>		27	35	mV	$I_C = 1A$ , $I_B = 100 \text{mA}^{(*)}$
saturation voltage			50	70	mV	$I_C = 1A$ , $I_B = 10mA^{(*)}$
			80	100	mV	$I_C = 2A$ , $I_B = 20mA^{(*)}$
			63	80	mV	$I_C = 2A$ , $I_B = 40mA^{(*)}$
			85	110	mV	I <sub>C</sub> = 4A, I <sub>B</sub> = 400mA <sup>(*)</sup> I <sub>C</sub> = 9A, I <sub>B</sub> = 450mA <sup>(*)</sup>
Base-Emitter saturation	1/		200 1040	250 1150	mV mV	
voltage	V <sub>BE(sat)</sub>					$I_C = 9A$ , $I_B = 450mA^{(*)}$
Base-Emitter turn-on voltage	V <sub>BE(on)</sub>		910	1050	mV	$I_C = 9A, V_{CE} = 2V^{(*)}$
Static forward current	h <sub>FE</sub>	300	450	900		$I_C = 100 \text{mA}, V_{CE} = 2V^{(*)}$
transfer ratio		260	390			$I_C = 2A, V_{CE} = 2V^{(*)}$
		130	175			$I_C = 9A, V_{CE} = 2V^{(*)}$
		50	75			$I_C = 15A, V_{CE} = 2V^{(*)}$
			30			$I_C = 20A, V_{CE} = 2V^{(*)}$
Transition frequency	f <sub>T</sub>		160		MHz	$I_C = 50 \text{mA}, V_{CE} = 10V$ f = 100MHz
Input capacitance	C <sub>ibo</sub>		297	400	pF	V <sub>EB</sub> = 0.5V, f = 1MHz <sup>(*)</sup>
Output capacitance	C <sub>obo</sub>		32.6	40	pF	V <sub>CB</sub> = 10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		129		ns	
Rise time	t <sub>r</sub>		96		ns	$I_C = 1A, V_{CC} = 10V,$
Storage time	t <sub>s</sub>		398		ns	$I_{B1} = -I_{B2} = 10 \text{mA}$
Fall time	t <sub>f</sub>		90		ns	

#### NOTES:

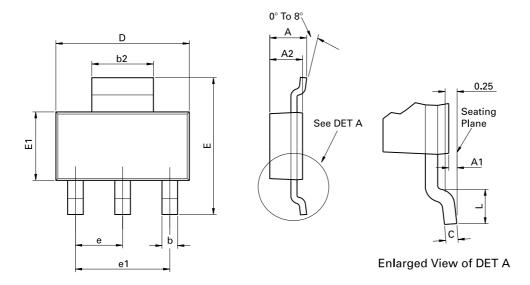
(\*) Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s; duty cycle  $\leq$  2%.

# **Typical characteristics**



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# Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.	Dilli.	Min.	Max.	Min.	Max.
Α	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	е	2.30 BSC		0.0905 BSC	
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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